Supertex inc.



Ordering Information

BV _{DSS} /	R _{DS(ON)} (max)	V _{GS(th)} (max)	I _{D(on)} (min)	Order Number / Package			
BV _{DGS}				TO-236AB*	TO-92	TO-243AA**	
250V	7.0Ω	2.0V	1.2A	TN5325K1	TN5325N3	TN5325N8	

Product marking for SOT-23:

N3C*

where * = 2-week alpha date code

Features

- Low threshold 2.0V max.
- ☐ Free from secondary breakdown
- Low power drive requirement
- Low C_{iss} and fast switching speeds
- Excellent thermal stability
- High input impedance and high gain
- Complementary N- and P-channel devices

Applications

- ☐ Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

Absolute Maximum Ratings

Drain-to-Source Voltage	BV _{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

^{*} Distance of 1.6 mm from case for 10 seconds.

Product marking for TO-243AA TN3C*

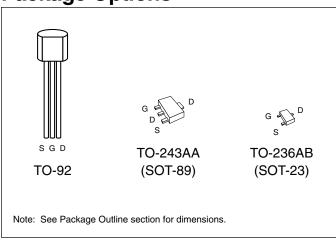
Where *=2-week alpha date code

Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Options



^{*} Same as SOT-23. All units shipped on 3,000 piece carrier tape reels.

^{**} Shipped on 2,000 piece carrier tape and reels.

Thermal Characteristics

Package	I _D (continuous)*	I _D (pulsed)	Power Dissipation @ T _A = 25°C	$ heta_{ m jc}$ $^{\circ}$ C/W	$ heta_{\sf ja}$ $^\circ$ C/W	I _{DR} *	I _{DRM}
TO-236AB	150mA	400mA	0.36W	200	350	150mA	400mA
TO-92	215mA	800mA	0.74W	125	170	215mA	800mA
TO-243AA	316mA	1.5A	1.6W**	15	78**	316mA	1.5A

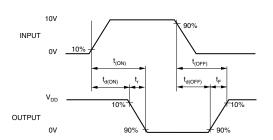
^{*} I_D (continuous) is limited by max rated T_j.

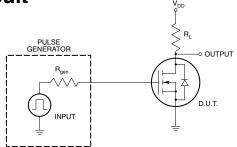
Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter	Min	Тур	Max	Unit	Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	250			V	$I_D = 100 \mu A, \ V_{GS} = 0 V$	
V _{GS(th)}	Gate Threshold Voltage	0.6		2.0	V	$V_{GS} = V_{DS}$, $I_D = 1mA$	
$\Delta V_{GS(th)}$	Change in V _{GS(th)} with Temperature			-4.5	mV/°C	$I_D = 1 \text{mA}, V_{GS} = V_{DS}$	
I _{GSS}	Gate Body Leakage			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
I _{DSS}	Zero Gate Voltage Drain Current			1.0	μΑ	$V_{GS} = 0V, V_{DS} = 100V$	
				10.0	μΑ	$V_{GS} = 0V$, $V_{DS} = Max$ Rating	
				1.0	mA	$V_{GS} = 0V$, $V_{DS} = 0.8$ Max Rating $T_A = 125$ °C	
I _{D(ON)}	ON-State Drain Current	0.6			Α	V _{GS} = 4.5V, V _{DS} = 25V	
		1.2				$V_{GS} = 10V, V_{DS} = 25V$	
R _{DS(ON)}	Static Drain-to-Source			8.0	Ω	V _{GS} = 4.5V, I _D = 150mA	
	ON-State Resistance			7.0	Ω	$V_{GS} = 10V, I_D = 1.0A$	
$\Delta R_{DS(ON)}$	Change in R _{DS(ON)} with Temperature			1.0	%/°C	$V_{GS} = 4.5V, I_D = 150mA$	
G _{FS}	Forward Transconductance	150			m [©]	$V_{DS} = 25V, I_{D} = 200mA$	
C _{ISS}	Input Capacitance			110			
C _{OSS}	Common Source Output Capacitance			60	pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	
C _{RSS}	Reverse Transfer Capacitance			23	1		
t _{d(ON)}	Turn-ON Delay Time			20	- ns	V _{DD} = 25V I _D = 150mA	
t _r	Rise Time			15			
t _{d(OFF)}	Turn-OFF Delay Time			25		$R_{GEN} = 25\Omega$	
t _f	Fall Time			25			
V_{SD}	Diode Forward Voltage Drop			1.8	V	$I_{SD} = 200 \text{mA}, V_{GS} = 0 \text{V}$	
t _{rr}	Reverse Recovery Time		300		ns	$I_{SD} = 200 \text{mA}, V_{GS} = 0 \text{V}$	

Notes:

Switching Waveforms and Test Circuit





11/12/01

^{**}Mounted on FR5 board. 25mm x 25mm x 1.57mm. Significant PD increase possible on ceramic substrate.

^{1.}All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

^{2.}All A.C. parameters sample tested.